Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A ferroelectric thin film formed of crystals in which directions of polarization axes are inconsistent with an applied electric field direction in a crystal system, the ferroelectric thin film comprising silicon, or silicon and germanium, in elements of ferroelectric.

2. (Currently Amended) A ferroelectric thin film formed of crystals in which directions of 180° domains are inconsistent with an applied electric field direction in a crystal system, the ferroelectric thin film comprising silicon, or silicon and germanium, in elements of ferroelectric.

3. (Currently Amended) A ferroelectric thin film formed of crystals in which directions of 90° domains are inconsistent with a direction perpendicular to an applied electric field direction in a crystal system, the ferroelectric thin film comprising silicon, or silicon and germanium, in elements of ferroelectric.

4-7. (Canceled)

8. (Currently Amended) The ferroelectric thin film as defined in claim 1, wherein polarization is arranged at a constant angle to the applied electric field direction to have the same polarization in the same applied electric field.

9. (Previously Presented) The ferroelectric thin film as defined in claim 1, formed of a polycrystal highly oriented in the applied electric field direction in a ferroelectric thin film plane.

10. (Previously Presented) The ferroelectric thin film as defined in claim 1, wherein a polarization axis distribution exhibits no anisotropy with respect to the applied electric field direction in a ferroelectric thin film plane.

11. (Previously Presented) The ferroelectric thin film as defined in claim 1, using: a tetragonal $Pb(Zr,Ti)O_3$ ferroelectric which is (111)-oriented along the applied electric field direction with respect to a ferroelectric thin film plane.

12. (Previously Presented) The ferroelectric thin film as defined in claim 1, using: a rhombohedral $Pb(Zr,Ti)O_3$ ferroelectric which is (001)-oriented along the applied electric field direction with respect to a ferroelectric thin film plane.

13. (Previously Presented) The ferroelectric thin film as defined in claim 1, using: a bismuth-layer-structured ferroelectric which is (111) or (110)-oriented along the applied electric field direction with respect to a ferroelectric thin film plane.

14. (Previously Presented) The ferroelectric thin film as defined in claim 1, using: an $SrBi_2Ta_2O_9$ ferroelectric which is (115), (111), or (110)-oriented along the applied electric field direction with respect to a ferroelectric thin film plane.

15. (Previously Presented) The ferroelectric thin film as defined in claim 1, using: a $Bi_4T_3O_{12}$ ferroelectric which is (117), (111), (107), or (317)-oriented along the applied electric field direction with respect to a ferroelectric thin film plane.

16-27. (Canceled)

28. (Previously Presented) A ferroelectric memory device using the ferroelectric thin film as defined in claim 1.

29. (Previously Presented) A ferroelectric piezoelectric device using the ferroelectric thin film as defined in claim 1.